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Data Sheet

LED Chip blue

EOLC-470-34

Rev. 05, 2020

Radiation	Type	Electrodes
blue	GaN / sapphire	P + N up

280 250 R50 280 310 100 P N All sizes in μm	Description - Substrate: sapphire, epitaxial layer: GaN based material - N bonding pad electrode: Au alloy - P bonding pad electrode: Au alloy Above drawing is not on real scale.
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Maximum Ratings

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I_F			20	mA
Peak forward current	$t_p \leq 50 \mu\text{s}$, $t_p/T = 1/2$	I_{FM}			100	mA

Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		3.3	3.5	V
Reverse current	$V_R = 5 \text{ V}$	I_R			1	μA
Luminous intensity*	$I_F = 20 \text{ mA}$	I_v	260	280	300	mcd
Dominant wavelength	$I_F = 20 \text{ mA}$	λ_p	467	470	473	nm
FWHM	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		30		nm

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire-bond side top

Art. No. 112 109



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.